

Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	3	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33\Omega$	- -	MAX.	10	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k\Omega$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	20	mA
				35	
I_H	$I_T=100mA$		MAX.	15	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	200	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=10V/\mu s$, $T_j=125$		MIN.	2.5	A/ms
t_{on}	$I_G=20mA$ $I_A=200mA$ $I_R=20mA$ $T_j=25$		TYP.	2.5	μs
t_{off}				25	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=5A$ $t_p=380\mu s$	$T_j=25$	1.65	V
V_{TO}	Threshold voltage	$T_j=125$	0.799	V
R_D	Dynamic resistance	$T_j=125$	151	$m\Omega$

 I_{DRM}
 $V_D=V_{DRM}$ $V_R=V_{RRM}$ $T_j=25$

ORDERING INFORMATION

J	ST	04	C	-800	SW
JieJie Microelectronics Co., Ltd.	Triacs	$I_{T(RMS)}:4A$	C:TO-220C	800: $V_{DRM} / V_{RRM} \geq 800V$	SW: $I_{GT1-3} \leq 10mA$

MARKING

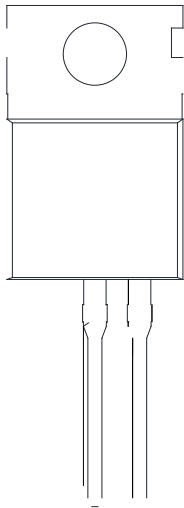


FIG.1: Maximum power dissipation versus RMS on-state current

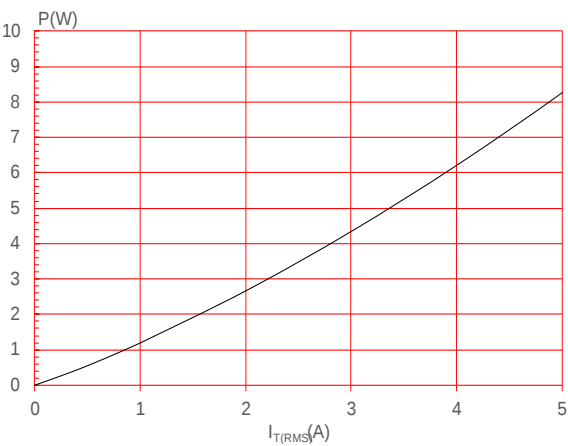


FIG.2: RMS on-state current versus case temperature

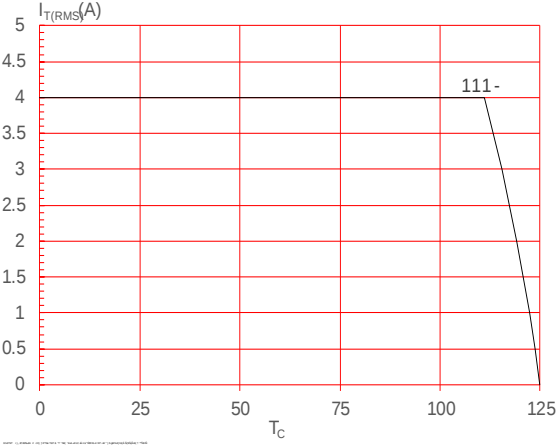


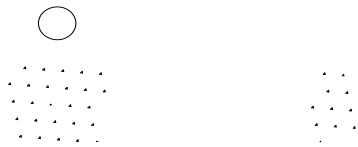
FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



ORDERING INFORMATION

Order code	Voltage V _{DRM} /V _{RRM} (V)	IGT(mA)	Package	Base q0 6.96 202e0.56 Tw 10.56 0dT		

PACKAGE MECHANICAL DATA



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